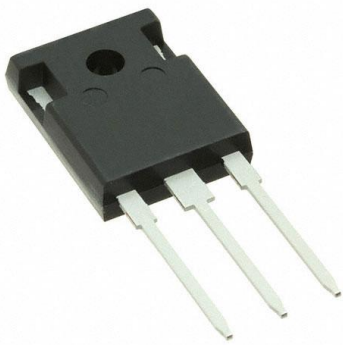


IKW75N65ET7XKSA1 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	IKW75N65ET7XKSA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IKW75N65ET7XKSA1
Description	IKW75N65ET7XKSA1
Detailed Description	IGBT Trench Field Stop 650 V 80 A 333 W Through Hole PG-T0247-3

This model IKW75N65ET7XKSA1 is available at DiGi Electronics.

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Manufacturer Product Number:

IKW75N65ET7XKSA1

Series:

TrenchStop™

IGBT Type:

Trench Field Stop

Current - Collector (Ic) (Max):

80 A

Vce(on) (Max) @ Vge, Ic:

1.65V @ 15V, 75A

Switching Energy:

2.17mJ (on), 1.23mJ (off)

Gate Charge:

435 nC

Test Condition:

400V, 75A, 4.70Ω, 15V

Operating Temperature:

-40°C ~ 175°C (Tj)

Qualification:

AEC-Q101

Package / Case:

TO-247-3

Base Product Number:

IKW75N65

Manufacturer:

Infineon Technologies

Product Status:

Active

Voltage - Collector Emitter Breakdown (Max):

650 V

Current - Collector Pulsed (Icm):

225 A

Power - Max:

333 W

Input Type:

Standard

Td (on/off) @ 25°C:

28ns/310ns

Reverse Recovery Time (trr):

100 ns

Grade:

Automotive

Mounting Type:

Through Hole

Supplier Device Package:

PG-TO247-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

Low loss Duopack: IGBT 7 with Trench and Fieldstop technology

Features

- $V_{CE} = 650\text{ V}$
- $I_C = 75\text{ A}$
- Very low $V_{CE,sat}$
- Low turn-off losses
- Short tail current
- Reduced EMI
- Very soft, fast recovery antiparallel diode
- Maximum junction temperature $T_{vjmax} = 175^\circ\text{C}$
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt7/>

Potential applications

- Servo drives
- General purpose drives (GPD)
- Industrial UPS
- Industrial SMPS
- Solar optimizer
- Solar string inverter

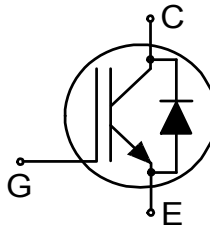
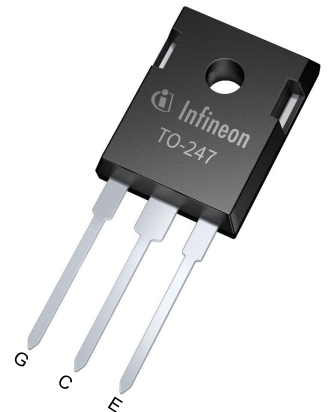
Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description

Package pin definition:

- Pin C & backside - Collector
- Pin E - Emitter
- Pin G - Gate



Type	Package	Marking
IKW75N65ET7	PG-TO247-3	K75EET7

IKW75N65ET7

Low loss Duopack: IGBT 7

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IKW75N65ET7

Low loss Duopack: IGBT 7

1 Package

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$				0.45	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$				0.6	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$	650	V	
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25\text{ °C}$	80	A
			$T_c = 100\text{ °C}$	78.5	
Pulsed collector current, t_p limited by T_{vjmax} ¹⁾	I_{Cpulse}		225	A	
Turn-off safe operating area ²⁾		$V_{CE} \leq 650\text{ V}$, $t_p = 1\text{ }\mu\text{s}$, $T_{vj} \leq 175\text{ °C}$	225	A	
Gate-emitter voltage	V_{GE}		± 20	V	
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10\text{ }\mu\text{s}$, $D < 0.01$	± 30	V	
Short-circuit withstand time	t_{SC}	$V_{GE} = 15\text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$	$V_{CC} \leq 330\text{ V}$, $T_{vj} = 100\text{ °C}$	5	μs
			$V_{CC} \leq 400\text{ V}$, $T_{vj} = 150\text{ °C}$	3	
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	333	W
			$T_c = 100\text{ °C}$	167	

1) Defined by design. Not subject to production test.

2) Clamped inductive load current test for each device, $I_C = 225\text{ A}$, $V_{CC} = 400\text{ V}$, $T_c = 25\text{ °C}$, $V_{GE} = 20\text{ V}$, $L = 80\text{ }\mu\text{H}$, $R_G = 10\text{ }\Omega$

IKW75N65ET7

Low loss Duopack: IGBT 7

2 IGBT

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.35	1.65	V
			$T_{vj} = 125\text{ °C}$	1.5		
			$T_{vj} = 175\text{ °C}$	1.6		
Gate-emitter threshold voltage	V_{GETh}	$I_C = 0.75\text{ mA}, V_{CE} = V_{GE}$	4.3	5	5.7	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		40	μA
			$T_{vj} = 175\text{ °C}$		1200	
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			100	nA
Transconductance	g_{fs}	$I_C = 75\text{ A}, V_{CE} = 20\text{ V}$		40		S
Short-circuit collector current	I_{SC}	$V_{CC} \leq 400\text{ V}, V_{GE} = 15\text{ V}, t_{SC} \leq 3\text{ }\mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 150\text{ °C}$		350		A
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1000\text{ kHz}$		4460		pF
Output capacitance	C_{oes}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1000\text{ kHz}$		135		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1000\text{ kHz}$		46		pF
Gate charge	Q_G	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, V_{CC} = 520\text{ V}$		435		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 4.7\text{ }\Omega, R_{G(off)} = 4.7\text{ }\Omega, L_\sigma = 32\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}, I_C = 75\text{ A}$	28		ns
			$T_{vj} = 25\text{ °C}, I_C = 37.5\text{ A}$	26		
			$T_{vj} = 175\text{ °C}, I_C = 75\text{ A}$	31		
			$T_{vj} = 175\text{ °C}, I_C = 37.5\text{ A}$	28		
Rise time (inductive load)	t_r	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V}, R_{G(on)} = 4.7\text{ }\Omega, R_{G(off)} = 4.7\text{ }\Omega, L_\sigma = 32\text{ nH}, C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}, I_C = 75\text{ A}$	25		ns
			$T_{vj} = 25\text{ °C}, I_C = 37.5\text{ A}$	13		
			$T_{vj} = 175\text{ °C}, I_C = 75\text{ A}$	30		
			$T_{vj} = 175\text{ °C}, I_C = 37.5\text{ A}$	18		

(table continues...)

IKW75N65ET7

Low loss Duopack: IGBT 7

2 IGBT

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 4.7\ \Omega,$ $R_{G(off)} = 4.7\ \Omega, L_{\sigma} = 32\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		310	ns
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		330	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		365	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		415	
Fall time (inductive load)	t_f	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 4.7\ \Omega,$ $R_{G(off)} = 4.7\ \Omega, L_{\sigma} = 32\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		15	ns
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		11	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		25	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		20	
Turn-on energy	E_{on}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 4.7\ \Omega,$ $R_{G(off)} = 4.7\ \Omega, L_{\sigma} = 32\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		2.17	mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.79	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		3.45	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		1.52	
Turn-off energy	E_{off}	$V_{CC} = 400\text{ V}, V_{GE} = 0/15\text{ V},$ $R_{G(on)} = 4.7\ \Omega,$ $R_{G(off)} = 4.7\ \Omega, L_{\sigma} = 32\text{ nH},$ $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		1.23	mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		0.56	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 75\text{ A}$		2.05	
			$T_{vj} = 175\text{ }^{\circ}\text{C},$ $I_C = 37.5\text{ A}$		1.11	

(table continues...)

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Low loss Duopack: IGBT 7

3 Diode

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Total switching energy	E_{ts}	$V_{CC} = 400\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 4.7\ \Omega$, $R_{G(off)} = 4.7\ \Omega$, $L_{\sigma} = 32\text{ nH}$, $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $I_C = 75\text{ A}$		3.4		mJ
			$T_{vj} = 25\text{ }^{\circ}\text{C}$, $I_C = 37.5\text{ A}$		1.35		
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $I_C = 75\text{ A}$		5.5		
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $I_C = 37.5\text{ A}$		2.63		
Operating junction temperature	T_{vj}		-40		175	$^{\circ}\text{C}$	

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25\text{ }^{\circ}\text{C}$	650	V	
Diode forward current, limited by T_{vjmax}	I_F	limited by bondwire	$T_C = 25\text{ }^{\circ}\text{C}$	80	A
			$T_C = 100\text{ }^{\circ}\text{C}$	74	
Diode pulsed current, t_p limited by T_{vjmax} ¹⁾	I_{Fpulse}		225	A	

1) Defined by design. Not subject to production test.

Table 5 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode forward voltage	V_F	$I_F = 75\text{ A}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		1.65	2	V
			$T_{vj} = 125\text{ }^{\circ}\text{C}$		1.6		
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		1.55		

(table continues...)

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Low loss Duopack: IGBT 7

3 Diode

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Diode reverse recovery time	t_{rr}	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		100		ns
			$T_{vj} = 25\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2725\text{ A}/\mu\text{s}$		70		
			$T_{vj} = 175\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		155		
			$T_{vj} = 175\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2260\text{ A}/\mu\text{s}$		125		
Diode reverse recovery charge	Q_{rr}	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		1.5		μC
			$T_{vj} = 25\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2725\text{ A}/\mu\text{s}$		1.15		
			$T_{vj} = 175\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		4.4		
			$T_{vj} = 175\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2260\text{ A}/\mu\text{s}$		3.36		
Diode peak reverse recovery current	I_{rrm}	$V_R = 400\text{ V}$	$T_{vj} = 25\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		22		A
			$T_{vj} = 25\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2725\text{ A}/\mu\text{s}$		34		
			$T_{vj} = 175\text{ °C}$, $I_F = 75\text{ A}$, $-di_F/dt = 1650\text{ A}/\mu\text{s}$		41		
			$T_{vj} = 175\text{ °C}$, $I_F = 37.5\text{ A}$, $-di_F/dt = 2260\text{ A}/\mu\text{s}$		43		

(table continues...)

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Low loss Duopack: IGBT 7

3 Diode

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	$V_R = 400 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_F = 75 \text{ A},$ $-di_F/dt = 1650 \text{ A}/\mu\text{s}$		480		A/ μs
			$T_{vj} = 25 \text{ }^\circ\text{C},$ $I_F = 37.5 \text{ A},$ $-di_F/dt = 2725 \text{ A}/\mu\text{s}$		600		
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_F = 75 \text{ A},$ $-di_F/dt = 1650 \text{ A}/\mu\text{s}$		590		
			$T_{vj} = 175 \text{ }^\circ\text{C},$ $I_F = 37.5 \text{ A},$ $-di_F/dt = 2260 \text{ A}/\mu\text{s}$		500		
Operating junction temperature	T_{vj}			-40		175	$^\circ\text{C}$

Note: *Maximum rated values: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*
Electrical Characteristic, at $T_{vj} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.
Dynamic test circuit, L_σ , C_σ from Fig. E. Energy losses include "tail" and diode reverse recovery.

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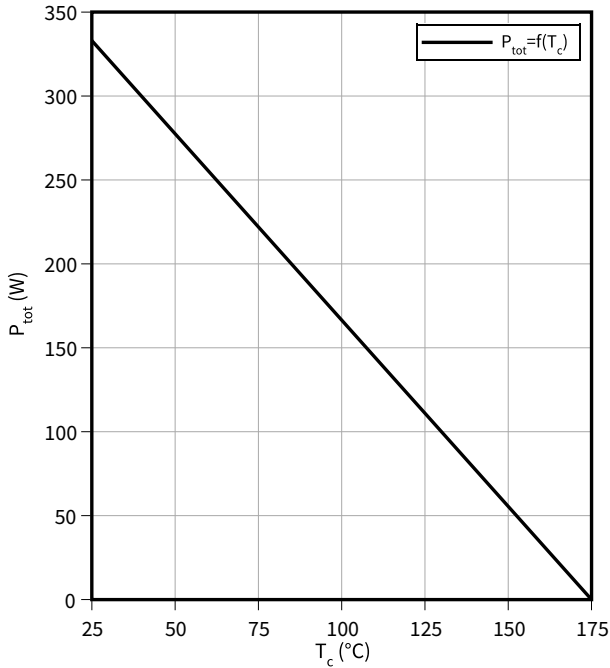
Low loss Duopack: IGBT 7

4 Characteristics diagrams

4 Characteristics diagrams

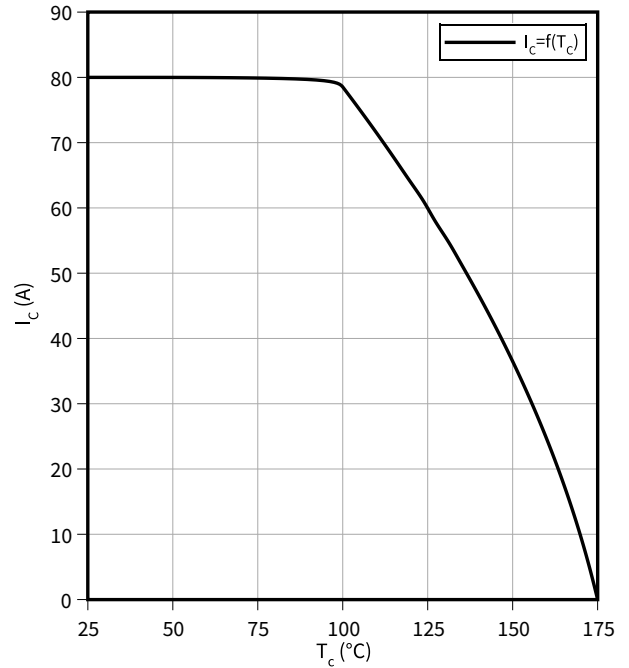
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$
 $T_{vj} \leq 175\text{ °C}$



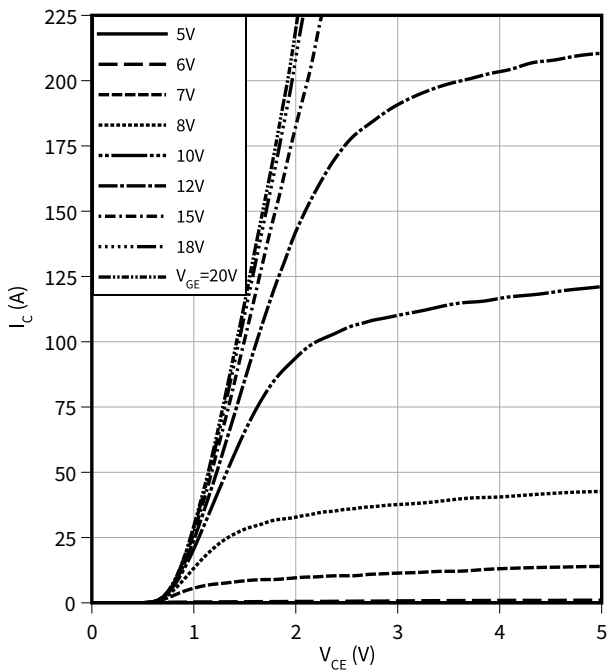
Collector current as a function of case temperature

$I_C = f(T_c)$
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



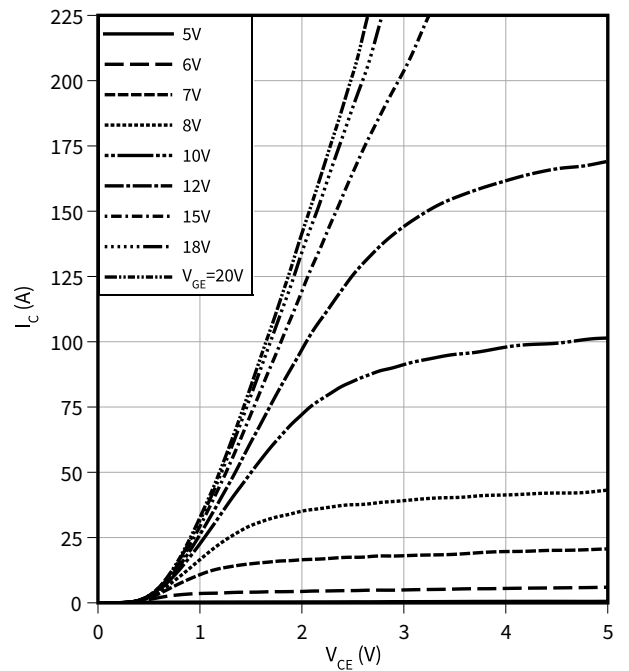
Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}$



Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 175\text{ °C}$



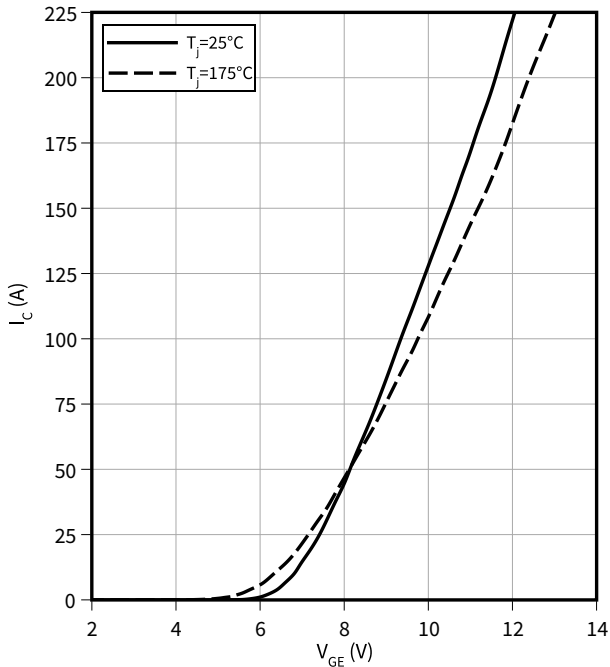
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Low loss Duopack: IGBT 7

4 Characteristics diagrams

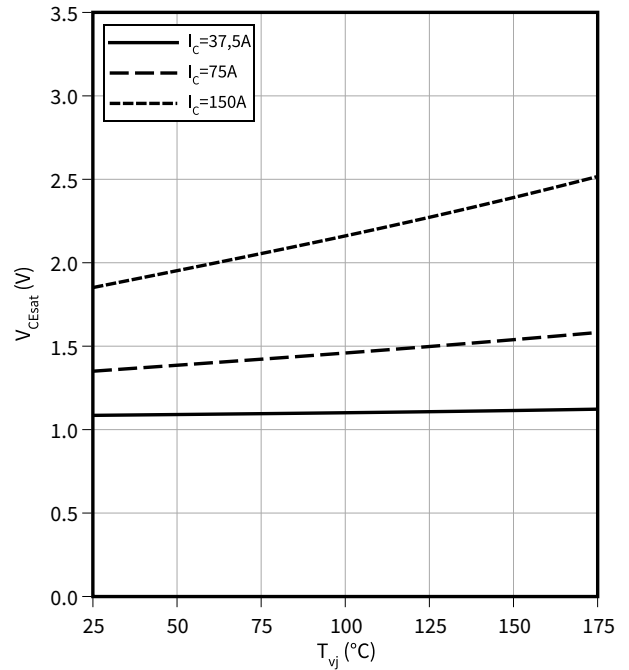
Typical transfer characteristic

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



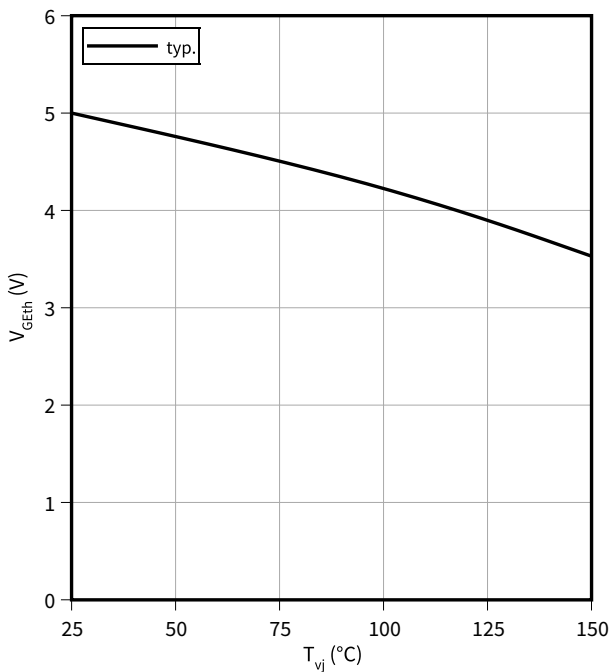
Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$
 $V_{GE} = 15\text{ V}$



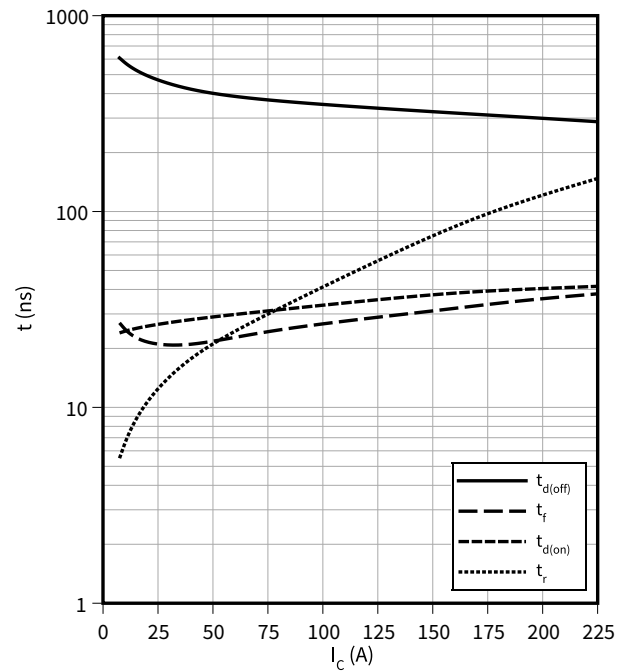
Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$
 $I_C = 0.75\text{ mA}$



Typical switching times as a function of collector current

$t = f(I_C)$
 $V_{CC} = 400\text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = 0/15\text{ V}, R_G = 4.7\ \Omega$



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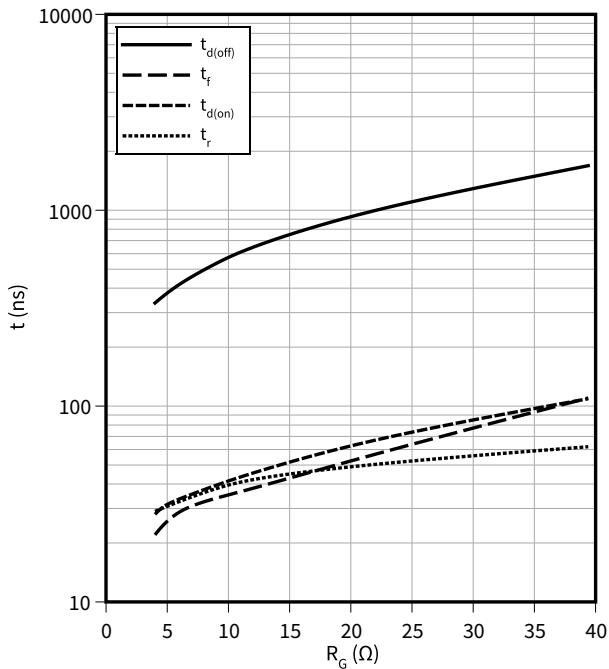
Low loss Duopack: IGBT 7

4 Characteristics diagrams

Typical switching times as a function of gate resistor

$t = f(R_G)$

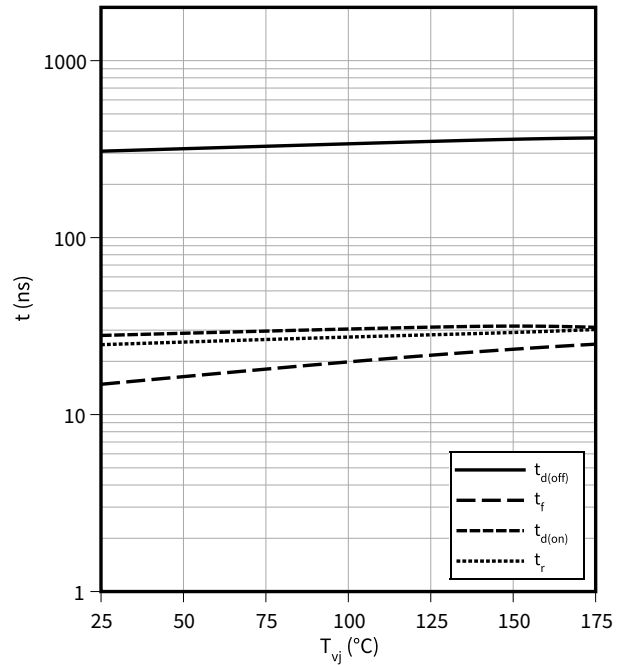
$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

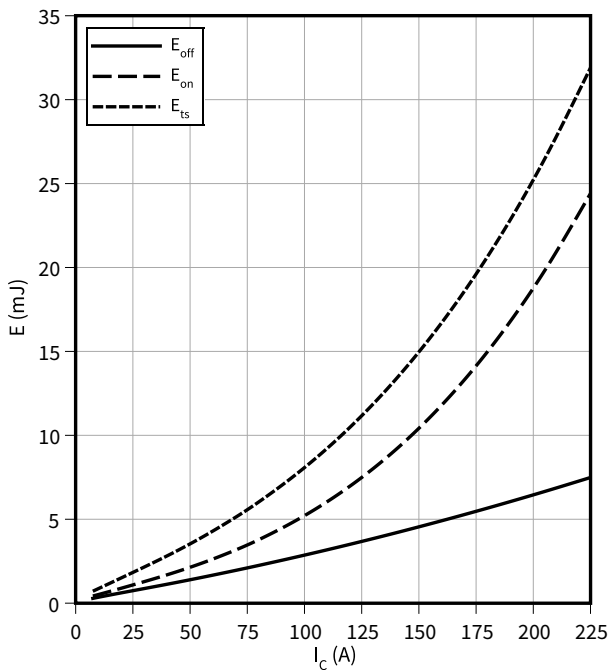
$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 4.7 \text{ } \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

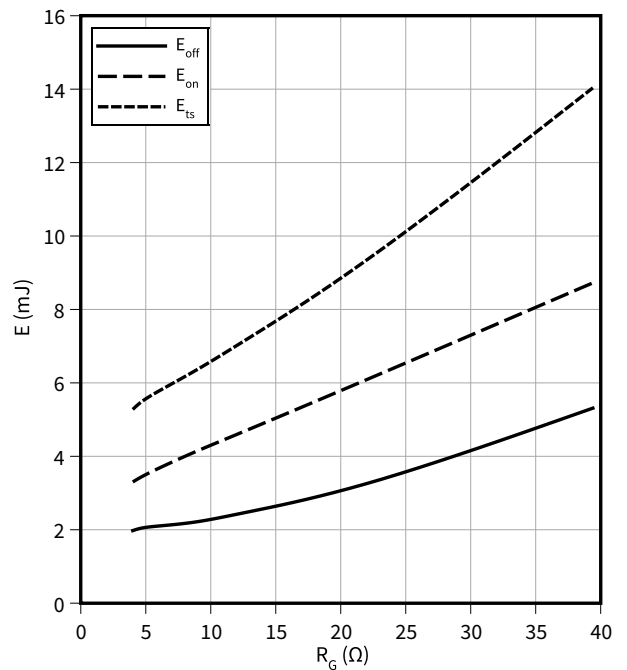
$V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}, R_G = 4.7 \text{ } \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

$I_C = 75 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$



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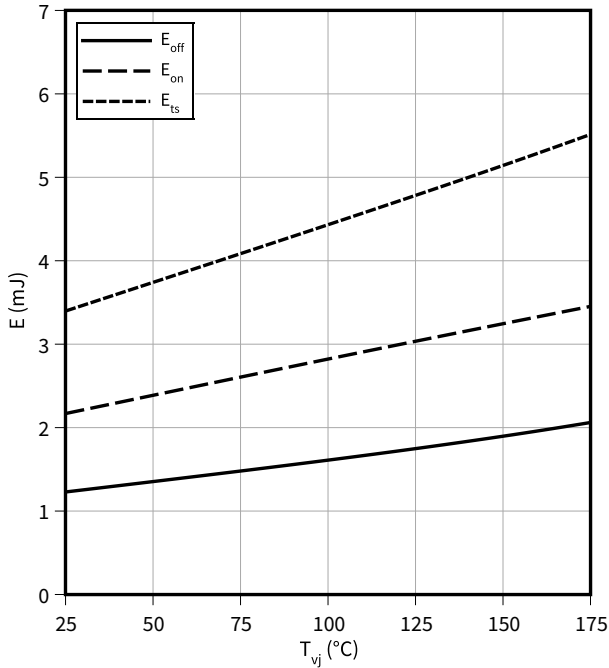
Low loss Duopack: IGBT 7

4 Characteristics diagrams

Typical switching energy losses as a function of junction temperature

$$E = f(T_{vj})$$

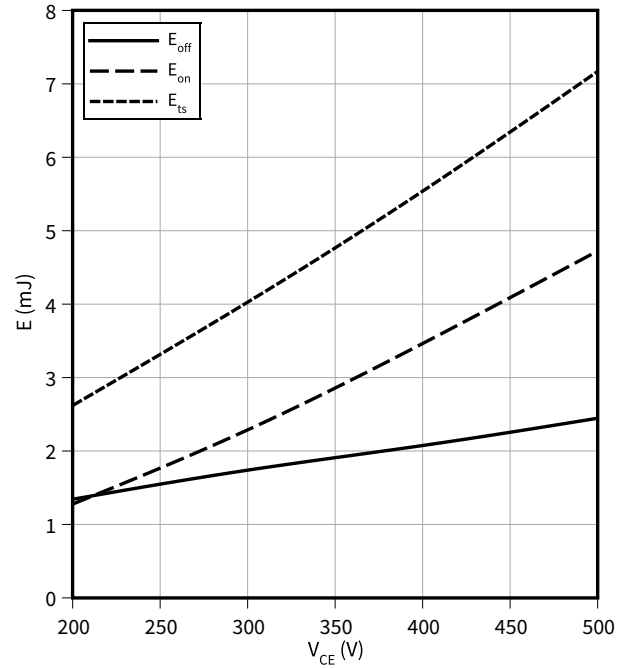
$I_C = 75 \text{ A}$, $V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 4.7 \Omega$



Typical switching energy losses as a function of collector emitter voltage

$$E = f(V_{CE})$$

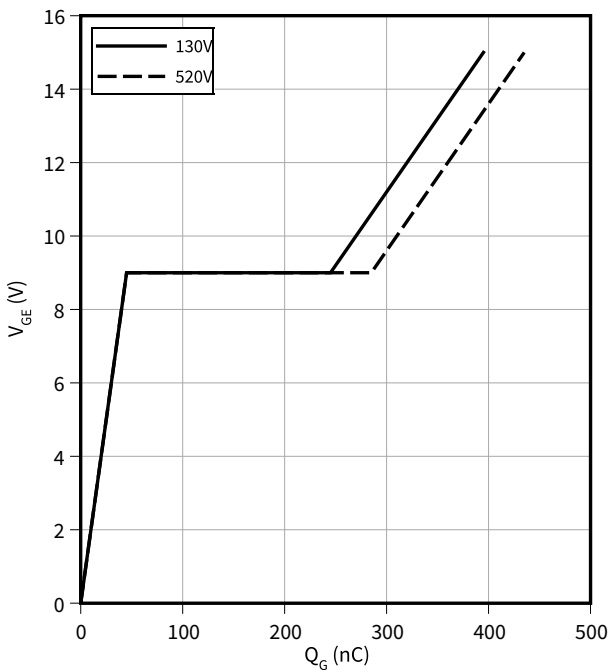
$I_C = 75 \text{ A}$, $T_{vj} = 175 \text{ °C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 4.7 \Omega$



Typical gate charge

$$V_{GE} = f(Q_G)$$

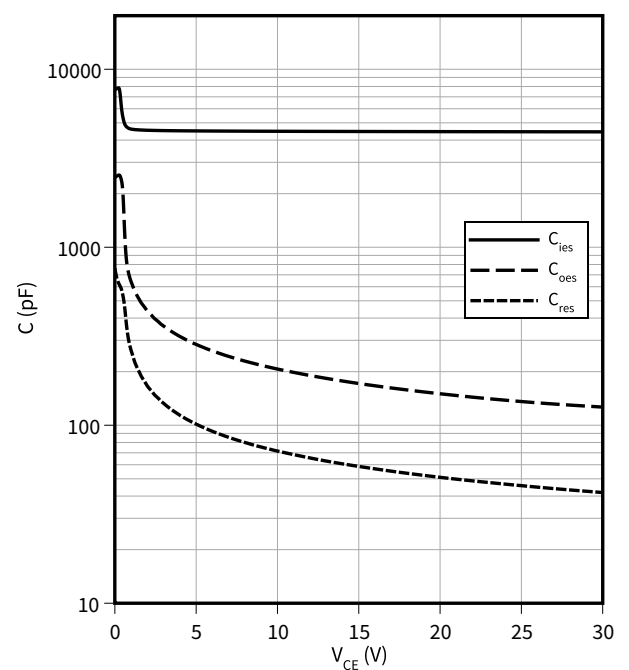
$I_C = 75 \text{ A}$



Typical capacitance as a function of collector-emitter voltage

$$C = f(V_{CE})$$

$f = 1000 \text{ kHz}$, $V_{GE} = 0 \text{ V}$



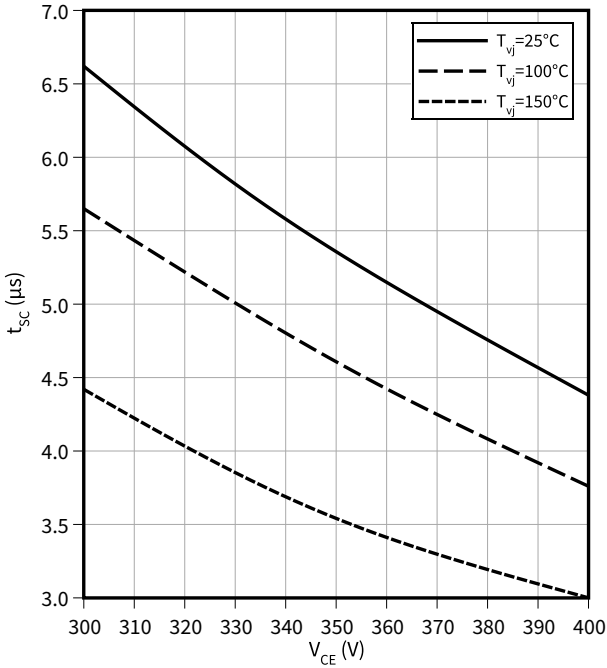
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4 Characteristics diagrams

Typical short circuit safe operating range as a function of collector-emitter voltage

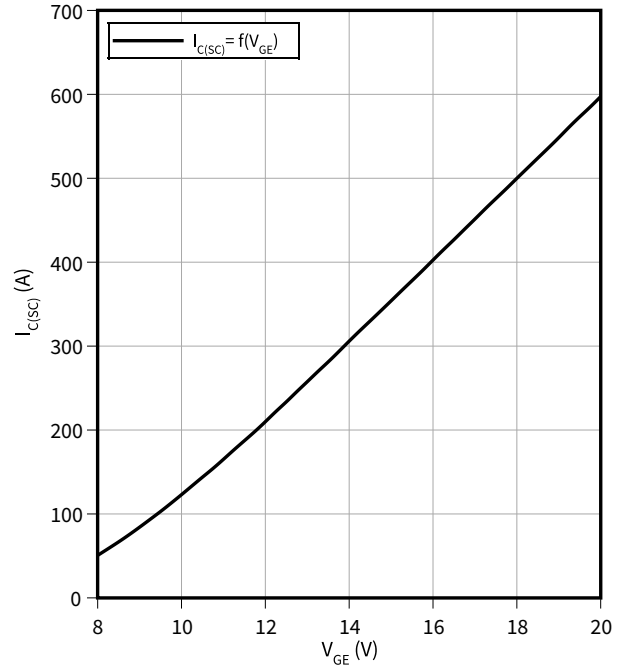
$$t_{SC} = f(V_{CE})$$



Typical short circuit collector current as a function of gate-emitter voltage

$$I_{C(SC)} = f(V_{GE})$$

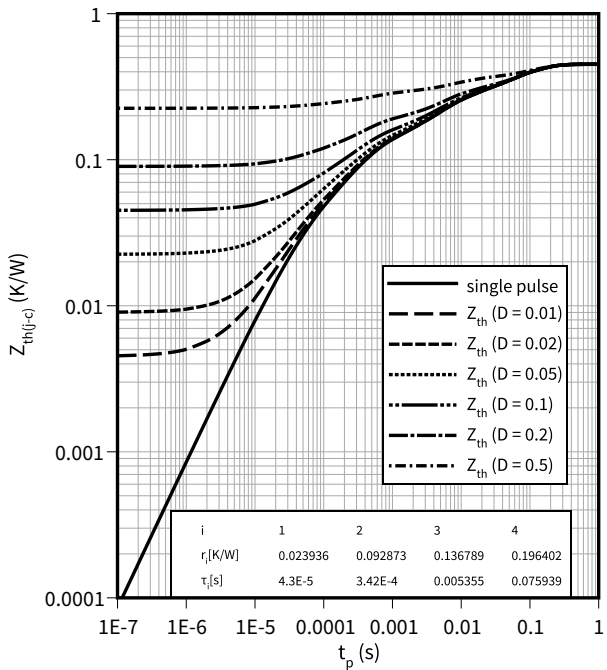
$T_{vj} = 150\text{ }^{\circ}\text{C}, V_{CE} \leq 400\text{ V}$



IGBT transient thermal impedance as a function of pulse width

$$Z_{th(j-c)} = f(t_p)$$

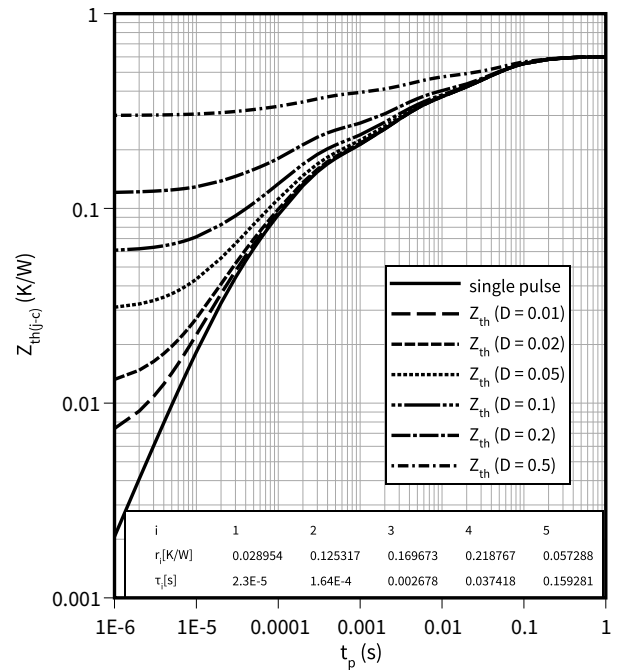
$$D = t_p/T$$



Diode transient thermal impedance as a function of pulse width

$$Z_{th(j-c)} = f(t_p)$$

$$D = t_p/T$$



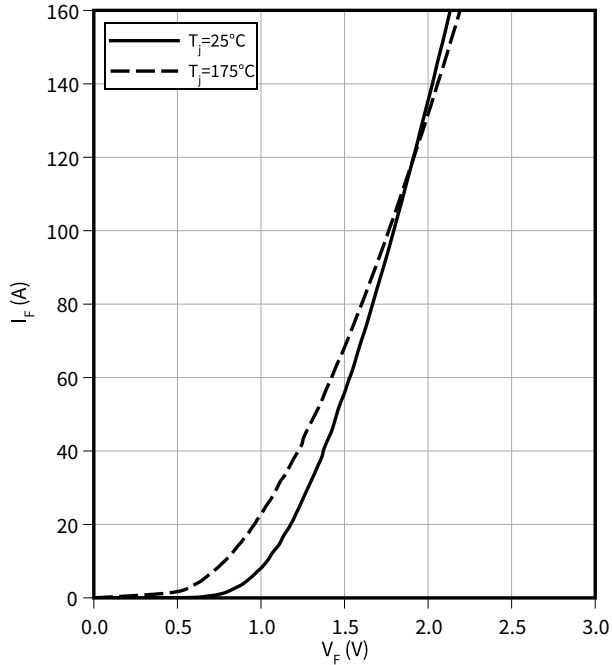
IKW75N65ET7

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4 Characteristics diagrams

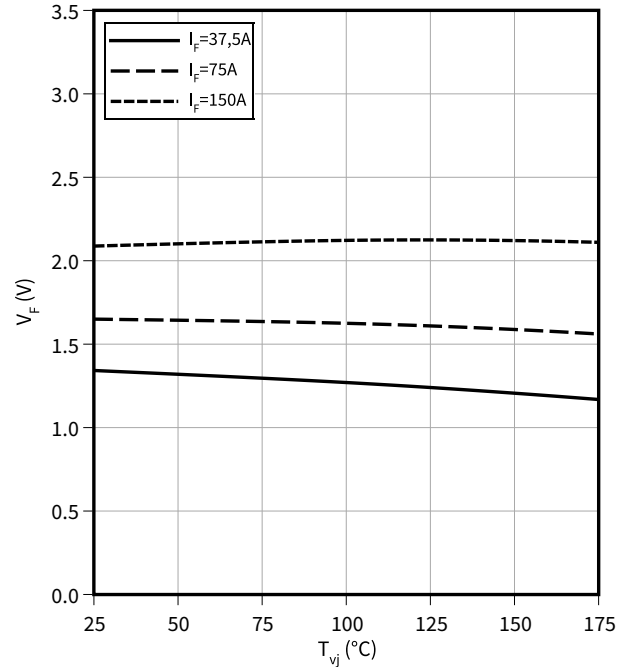
Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$



Typical diode forward voltage as a function of junction temperature

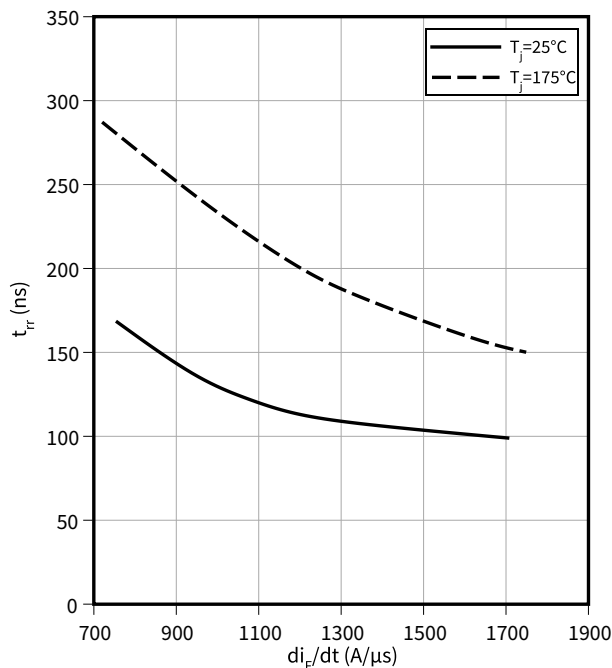
$$V_F = f(T_{vj})$$



Typical reverse recovery time as a function of diode current slope

$$t_{rr} = f(di_F/dt)$$

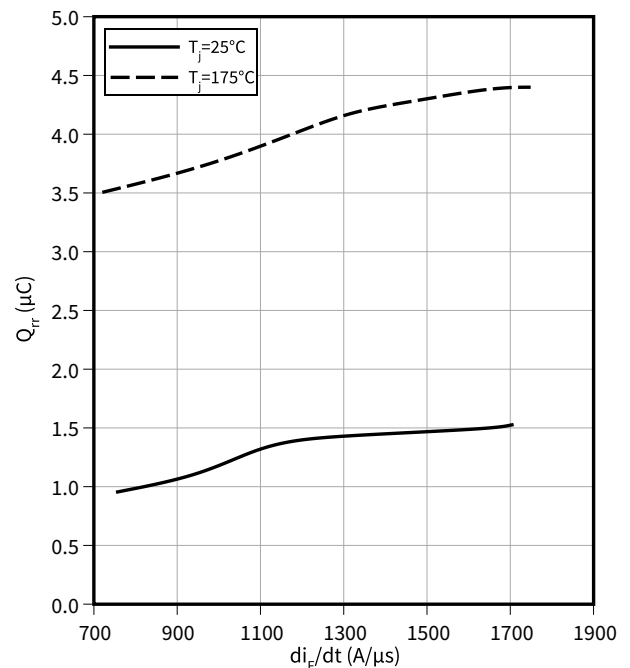
$V_R = 400\text{ V}, I_F = 75\text{ A}$



Typical reverse recovery charge as a function of diode current slope

$$Q_{rr} = f(di_F/dt)$$

$V_R = 400\text{ V}, I_F = 75\text{ A}$



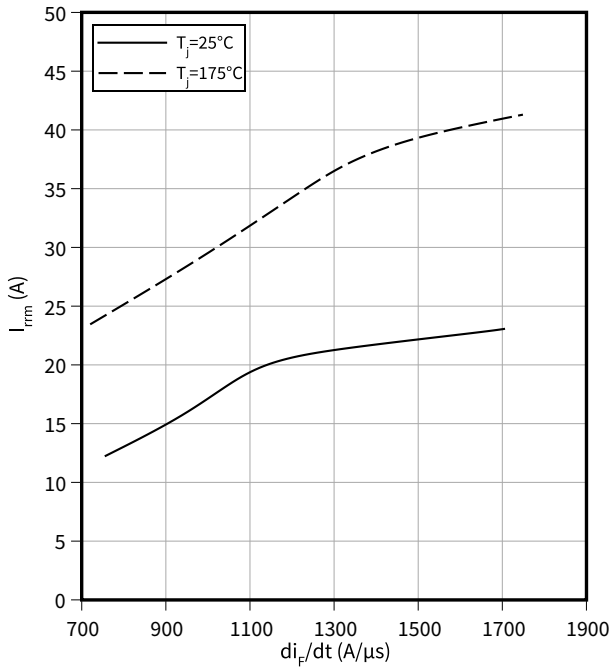
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4 Characteristics diagrams

Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

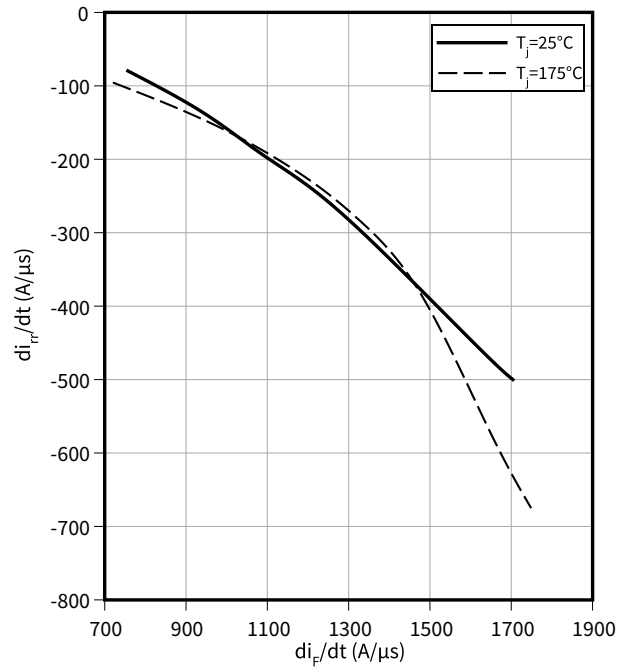
$V_R = 400\text{ V}, I_F = 75\text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

$V_R = 400\text{ V}, I_F = 75\text{ A}$



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5 Package outlines

5 Package outlines

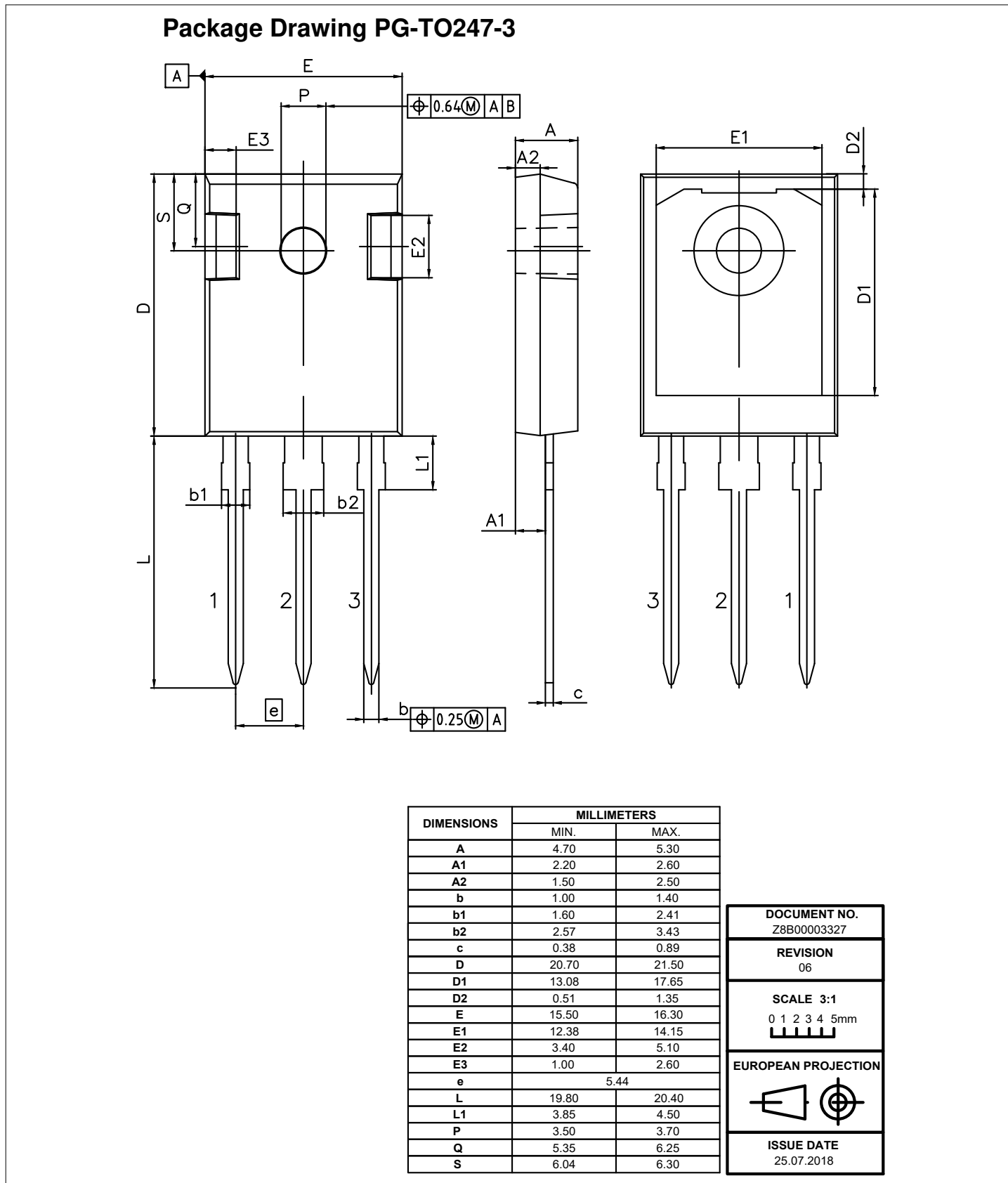


Figure 1

IKW75N65ET7
Low loss Duopack: IGBT 7

6 Testing conditions

6 Testing conditions

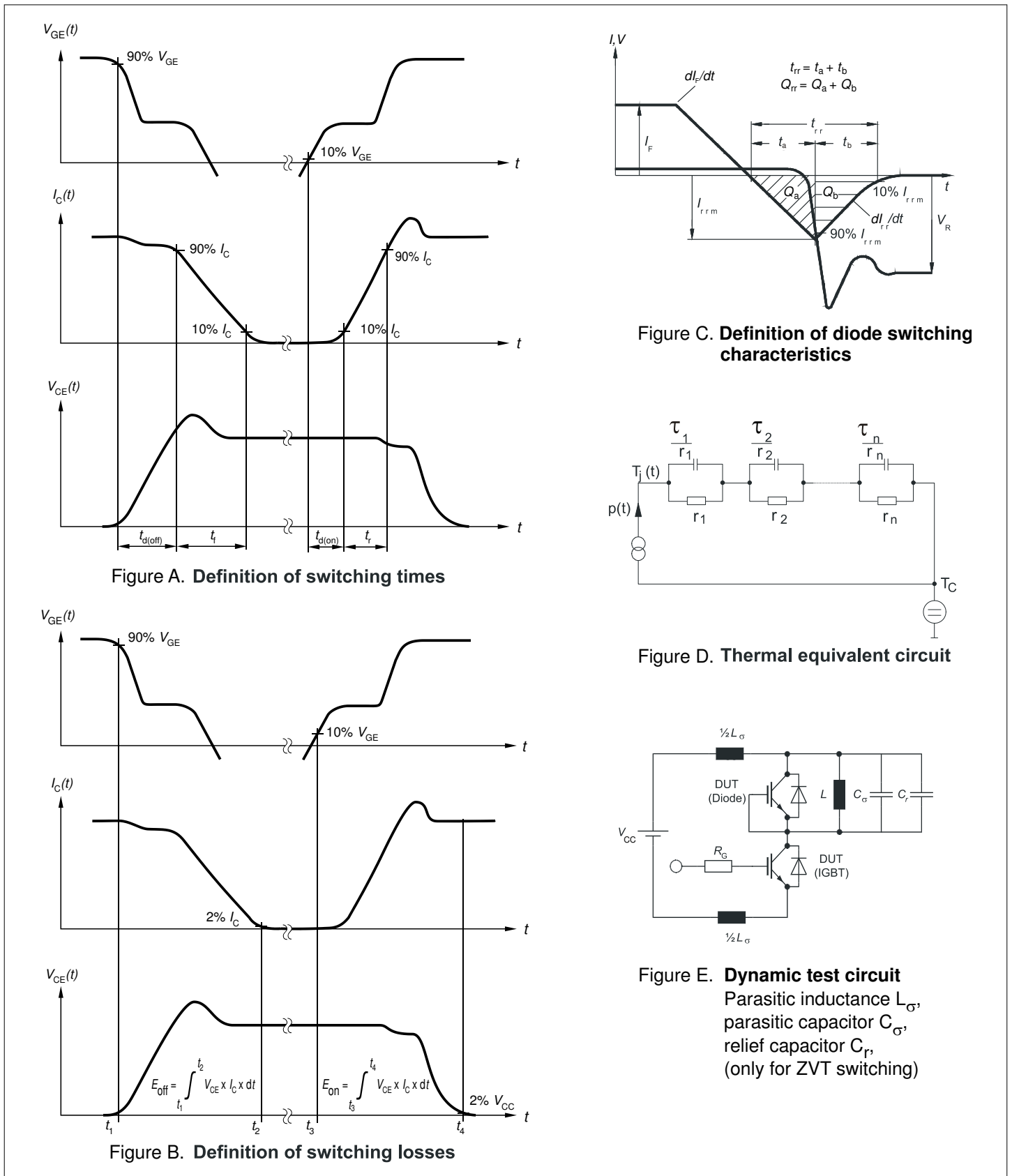


Figure 2

IKW75N65ET7

Low loss Duopack: IGBT 7

Revision history

Revision history

Document revision	Date of release	Description of changes
V0.1	2019-10-25	Target Data Sheet
V1.1	2020-04-20	Preliminary data sheet
V2.1	2020-05-12	Final data sheet
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2021-06-29	Change of potential applications and new diagram added (t_{SC} as function of V_{CE})
1.10	2023-01-26	Feature list corrections Editorial changes

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